## CMOS LOGIC

Inside the CMOS inverter, no $I_{D}$ current flows through transistors when input is logic 1 or logic 0 , because

- the NMOS transistor is cutoff for logic $0(0 \mathrm{~V})$ input
- the PMOS transistor is cutoff for logic $1\left(\mathrm{~V}_{\mathrm{DD}}\right)$ input
- current through the "turned on" transistor has nowhere to go if next stage consists of transistor gates


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\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{DD}}
$$

- NMOS transistor cutoff (since $\mathrm{V}_{\mathrm{GS}(\mathrm{N})}=\mathrm{V}_{\mathrm{IN}}=0 \mathrm{~V}$ ) "acts as open circuit"
- PMOS transistor "on"
$\left(\mathrm{V}_{G S(P)}=\mathrm{V}_{I N}-\mathrm{V}_{\mathrm{DD}}=-\mathrm{V}_{\mathrm{DD}}\right)$
but $I_{D(P)}=0 \mathrm{~A}=>\mathrm{V}_{\mathrm{DS}(\mathrm{P})}=0 \mathrm{~V}$
$I_{D(N)}\left(=-I_{D(P)}\right)$

- PMOS transistor cutoff $\left(V_{G S(P)}=V_{I N}-V_{D D}=0 V\right)$ "acts as open circuit"
- NMOS transistor "on"
$\left(\mathrm{V}_{\mathrm{GS}(\mathrm{N})}=\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{DD}}\right)$ but $I_{D(N)}=0 A \Rightarrow V_{D S(N)}=0 \mathrm{~V}$
$I_{D(N)}\left(=-I_{D(P)}\right)$



## EASY MODEL FOR LOGIC ANALYSIS

There is a simpler model for the behavior of transistors in a CMOS logic circuit, which applies when the input to the logic circuit is fully logic 0 or fully logic 1.



We can use the model to quickly determine the logical operation of a CMOS circuit (but we cannot use it to find circuit currents or voltages that will occur for mid-range input voltages).

## REVISIT CMOS INVERTER WITH SIMPLE LOGIC MODEL

Fill in the switch positions below...


Verify the logical operation of the CMOS NAND circuit:


Verify the logical operation of the CMOS NAND circuit:



Verify the logical operation of the CMOS NOR circuit:


Verify the logical operation of the CMOS NOR circuit:


## PULL-UP AND PULL-DOWN DEVICES

In our logic circuits, the NMOS transistor sources are connected to ground, and the PMOS sources are connected to $\mathrm{V}_{\mathrm{DD}}$.

Notice that when NMOS transistors are "on" (when $\mathrm{V}_{\text {GSN }}=\mathrm{V}_{\mathrm{DD}}$ ) $\mathrm{V}_{\text {DSN }}$ is shorted by switch, helping connect output to ground.

The NMOS transistor functions as a pull-down device; when active, it brings the output to 0 V .

When PMOS transistors are "on" (when $\mathrm{V}_{\mathrm{GSP}}=-\mathrm{V}_{\mathrm{DD}}$ )
$V_{D S P}$ is shorted by switch, helping connect output to $V_{D D}$.
The PMOS transistor functions as a pull-up device; when active, it brings the output to $\mathrm{V}_{\mathrm{DD}}$.

## LIMITATIONS OF SWITCH MODEL



In reality, the pull-up devices must have some $\mathrm{V}_{\mathrm{DS}}$ voltage

Similarly, the pull-down devices must have some $\mathrm{V}_{\mathrm{DS}}$ voltage and current flow to bring the output to ground since natural capacitance must be discharged.

This is GATE DELAY.

## LIMITATIONS OF SWITCH MODEL

Suppose one needed to fully analyze the circuit for intermediate input voltages.



- $\mathrm{NMOS}_{1}$ barely on $\left(\mathrm{V}_{\mathrm{DS}(\mathrm{N} 2)} \geq 0\right)$ => saturation
- $\mathrm{NMOS}_{2}$ fully on, but $\mathrm{NMOS}_{1}$ limits $\mathrm{I}_{\mathrm{D}}$ to small value => triode
- $\mathrm{PMOS}_{2}$ on, but $\mathrm{NMOS}_{1}$ and $\mathrm{PMOS}_{1}$ make $\mathrm{I}_{\mathrm{D}}$ small => triode

